



Solid State Devices, Inc.

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SED20HB100 SED20HE100

**20 AMP
100 VOLTS
SCHOTTKY RECTIFIER**

Designer's Data Sheet

Part Number / Ordering Information^{1/}

SED20 _ **100** _

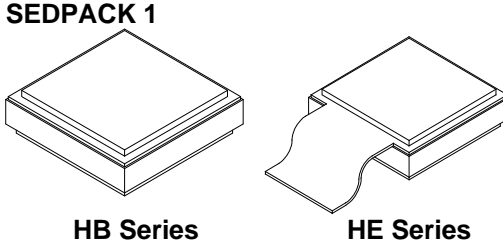
 L **Screening**^{2/} = None
 TX = TX Level
 TXV = TXV Level
 S = S Level

 L **Configuration**
 HB = without lead
 HE = with lead

- FEATURES:**
- Low Reverse Leakage
 - Low Forward Voltage Drop
 - Hermetically Sealed Power Surface Mount Package
 - Guard Ring for Overvoltage Protection
 - Eutectic Die Attach
 - 175°C Operating Temperature
 - TX, TXV, and Space Level Screening Available^{2/}

MAXIMUM RATINGS		Symbol	Value	Units
Peak Repetitive Reverse Voltage and DC Blocking Voltage		V_{RRM} V_{RWM} V_R	100	Volts
Average Rectified Forward Current (Resistive Load, 60 Hz, Sine Wave, $T_A = 100^\circ\text{C}$)		I_O	20	Amps
Peak Surge Current (8.3 ms Pulse, Half Sine Wave, Superimposed on I_O , Allow Junction to Reach Equilibrium between Pulses, $T_A = 25^\circ\text{C}$)		I_{FSM}	175	Amps
Operating and Storage Temperature		T_{OP} & T_{stg}	-55 to +175	°C
Maximum Thermal Resistance Junction to Case		$R_{\theta JC}$	1.25	°C/W

Notes:
 1/ For Ordering Information, Price, Operating Curves, and Availability – Contact Factory.
 2/ Screening to MIL-PRF-19500.





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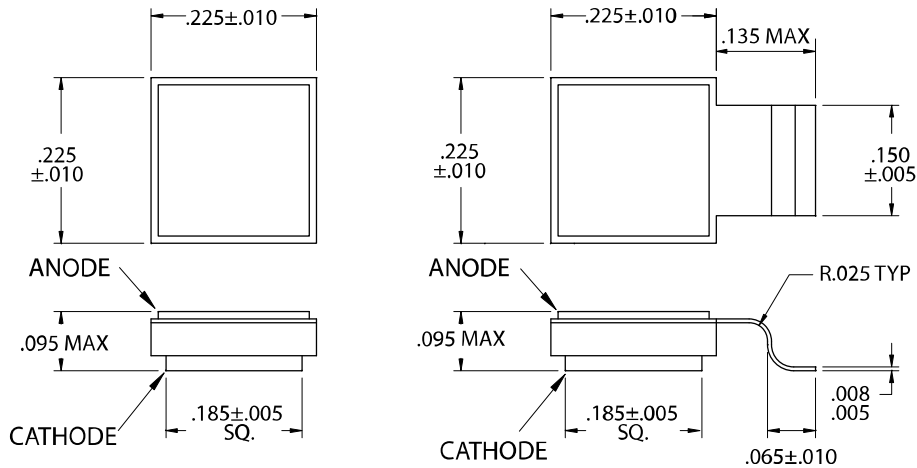
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ELECTRICAL CHARACTERISTICS	Symbol	Maximum	Unit	
Instantaneous Forward Voltage Drop ($T_A = 25^\circ\text{C}$, 300-500 μsec Pulse)	$I_F = 10 A_{DC}$	V_{F1}	0.78	V_{DC}
	$I_F = 20 A_{DC}$	V_{F2}	0.87	
Instantaneous Forward Voltage Drop ($T_A = +125^\circ\text{C}$, 300-500 μsec Pulse)	$I_F = 10 A_{DC}$	V_{F1}	0.63	V_{DC}
	$I_F = 20 A_{DC}$	V_{F2}	0.70	
Reverse Leakage Current (Rated V_R , 300 μsec pulse minimum)	$T_A = 25^\circ\text{C}$	I_{R1}	1.5	mA
	$T_A = 125^\circ\text{C}$	I_{R2}	10	
Junction Capacitance ($V_R = 10 V_{DC}$, $T_A = 25^\circ\text{C}$, $f = 1 \text{ MHz}$)	C_J	600	pF	

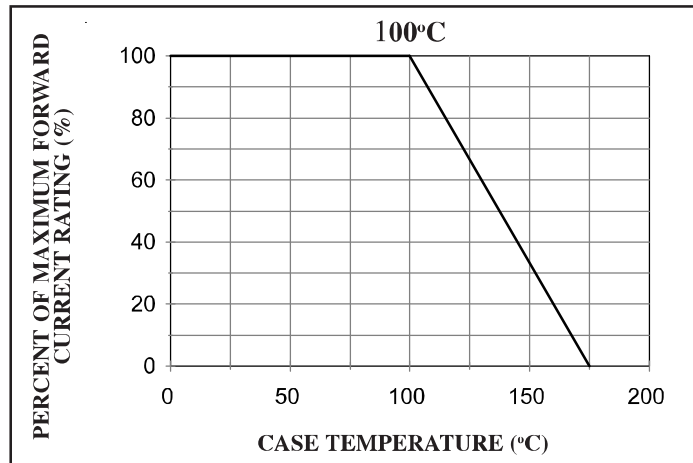
CASE OUTLINE: SED10HB45

CASE OUTLINE: SED10HE45



TYPICAL OPERATING CURVES

($T_A = 25^\circ\text{C}$ unless otherwise specified)



NOTE: All specifications are subject to change without notification. SCD's for these devices should be reviewed by SSDI prior to release.

DATA SHEET #: SH0024B

DOC